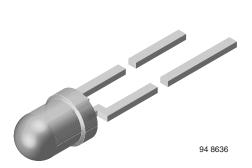
VSLY3850

www.vishay.com

Vishay Semiconductors

High Speed Infrared Emitting Diode, 850 nm, Surface Emitter Technology



As part of the SurfLight[™] portfolio, the VSLY3850 is an infrared, 850 nm emitting diode based on GaAlAs surface

emitter chip technology with extreme high radiant intensity,

high optical power and high speed, molded in a clear,

FEATURES

- Package type: leaded
- Package form: T-1, clear epoxy
- Dimensions: Ø 3 mm
- Peak wavelength: $\lambda_p = 850 \text{ nm}$
- High speed
- High radiant power
- · High radiant intensity
- Angle of half intensity: $\phi = \pm 18^{\circ}$
- · Suitable for high pulse current operation
- · Good spectral matching with CMOS cameras
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Infrared radiation source for operation with CMOS cameras
- High speed IR data transmission
- 3D TV application
- Light curtains

PRODUCT SUMMARY COMPONENT l_e (mW/sr) φ (deg) λ_p (nm) t_r (ns) VSLY3850 70 ± 18 850 10

Note

DESCRIPTION

untinted T1 plastic package.

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION							
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM				
VSLY3850	Bulk	MOQ: 5000 pcs, 5000 pcs/bulk	T-1				
VSLY3850-ASZ	Ammopack	MOQ: 10 000 pcs, 2000 pcs/box	T-1				

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS (T _{amb} = 25 °C, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT		
Reverse voltage		V _R	5	V		
Forward current		I _F	100	mA		
Peak forward current	$t_p/T = 0.5, t_p = 100 \ \mu s$	I _{FM}	200	mA		
Surge forward current	t _p = 100 μs	I _{FSM}	1	A		
Power dissipation		Pv	190	mW		
Junction temperature		Tj	100	°C		
Operating temperature range		T _{amb}	-40 to +85	°C		
Storage temperature range		T _{stg}	-40 to +100	°C		
Soldering temperature	$t \leq 5 \text{ s}, 2 \text{ mm}$ from case	T _{sd}	260	°C		
Thermal resistance junction / ambient	J-STD-051, leads 7 mm, soldered on PCB	R _{thJA}	300	K/W		

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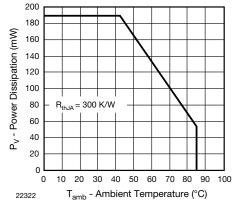


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

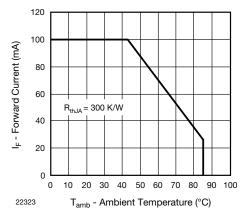


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified)								
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Forward voltage	l _F = 100 mA, t _p = 20 ms	V _F	-	1.65	1.9	V		
	I _F = 1 A, t _p = 100 μs	V _F	-	2.9	-	V		
Temperature coefficient of V _F	I _F = 1 mA	TK _{VF}	-	-1.45	-	mV/K		
	I _F = 10 mA	TK _{VF}	-	-1.25	-	mV/K		
Reverse current		I _R	Not designed for reverse operation			μA		
Junction capacitance	$V_R = 0 V$, f = 1 MHz, E = 0 mW/cm ²	CJ	-	125	-	pF		
Radiant intensity	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	l _e	35	70	105	mW/sr		
	I _F = 1 A, t _p = 100 μs	l _e	-	600	-	mW/sr		
Radiant power	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	фе	-	55	-	mW		
Temperature coefficient of radiant power	I _F = 1 mA	TK_{\phie}	-	-0.35	-	%/K		
Angle of half intensity		φ	-	± 18	-	deg		
Peak wavelength	I _F = 30 mA	λρ	840	850	870	nm		
Spectral bandwidth	I _F = 30 mA	Δλ	-	30	-	nm		
Temperature coefficient of Ip	I _F = 30 mA	TK _{λp}	-	0.25	-	nm		
Rise time	$I_F = 100 \text{ mA}, 20 \% \text{ to } 80 \%$	t _r	-	10	-	ns		
Fall time	$I_F = 100 \text{ mA}, 20 \% \text{ to } 80 \%$	t _f	-	10	-	ns		



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BASIC CHARACTERISTICS (Tamb = 25 °C, unless otherwise specified)

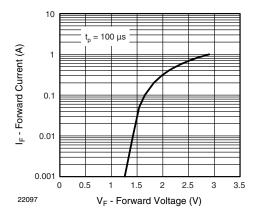


Fig. 3 - Forward Current vs. Forward Voltage

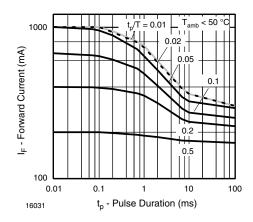


Fig. 4 - Pulse Forward Current vs. Pulse Duration

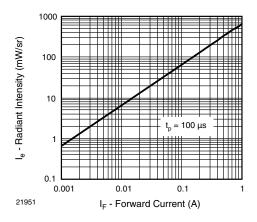


Fig. 5 - Radiant Intensity vs. Forward Current

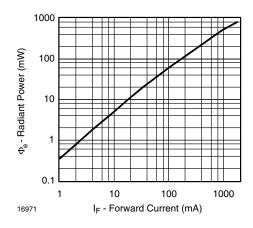


Fig. 6 - Radiant Power vs. Forward Current

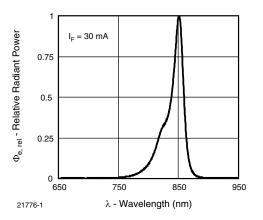


Fig. 7 - Relative Radiant Power vs. Wavelength

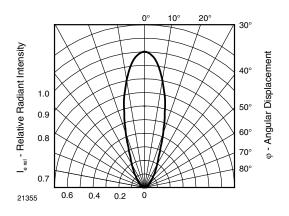


Fig. 8 - Relative Radiant Intensity vs. Angular Displacement

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For technical questions, contact: emittertechsupport@vishay.com

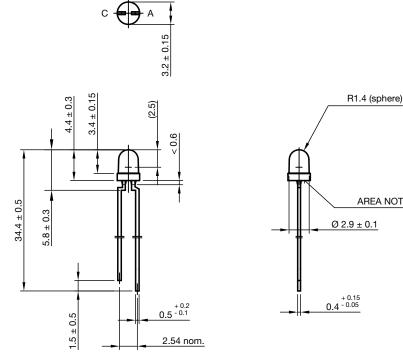
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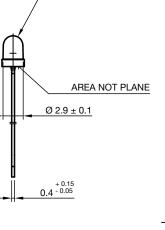
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PACKAGE DIMENSIONS in millimeters







technical drawings according to DIN specifications

Drawing-No.: 6.544-5264.01-4 Issue: 4; 28.07.14



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